Low Noise Amplifier with Bypass Switch for LTE High Band

FEATURES

- Operating frequency 2300MHz to 2690MHz
- Noise figure(NF) =1.0dB
- High power gain =13.4dB
- Insertion Loss in bypass mode =4dB
- Gain mode IIP3ib =+5dBm
- Gain mode input 1dB-compression point=-2dBm
- Bypass mode input 1dB-compression point= +8dBm
- Supply voltage: 1.5V to 3.3V
- Gain mode current 9mA
- Bypass mode current <1uA
- Input and output DC decoupled
- Requires only one input matching inductor
- Integrated matching for the output
- FCDFN 1.1mmX0.7mmX0.37mm -6L package
- 2kV HBM ESD protection (including RFIN and RFOUT pin)

GENERAL DESCRIPTION

- The AW15208HFDR is a Low Noise Amplifier with bypass designed for LTE receiver applications. The AW15208HFDR requires only one external input matching inductor, reduces assembly complexity and the PCB area, enabling a cost-effective solution.
- The AW15208HFDR achieves low noise figure, high linearity, high gain, over a wide range of supply voltages from 1.5V up to 3.3V. All these features make AW15208HFDR an excellent choice for LTE LNA as it improves sensitivity with low noise figure and high gain, provides better immunity against jammer signals with high linearity, reduces filtering requirement of preceding stage and hence reduces the overall cost.
- The AW15208HFDR is available in a small lead-free, RoHS-Compliant, FCDFN 1.1mmX0.7mmX0.37 mm -6L package.

APPLICATIONS

- Cell phones
- Tablets
- Other RF front-end modules

TYPICAL APPLICATION CIRCUIT

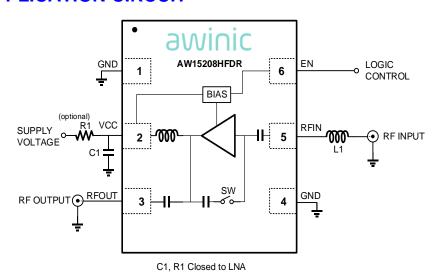


Figure 1 Typical Application Circuit of AW15208HFDR



PIN CONFIGURATION AND TOP MARK

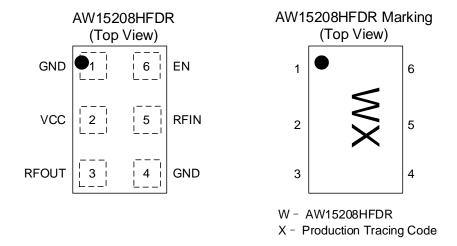


Figure 2 Pin Configuration and Top Mark

PIN DEFINITION

No.	NAME	DESCRIPTION
1	GND	Ground
2	VCC	Supply connection
3	RFOUT	RF output
4	GND	Ground
5	RFIN	RF input
6	EN	EN (high level) supports 1.8V/2.8V IO with internal 150Kohm pull-down resistor



FUNCTIONAL BLOCK DIAGRAM

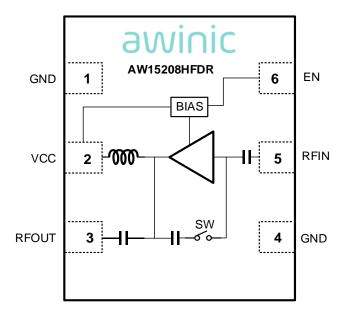


Figure 3 Functional Block Diagram

ORDERING INFORMATION

Part Number	Temperature	Package	Marking	Moisture Sensitivity Level	Environmental Information	Delivery Form
AW15208HFDR	-40℃~85℃	FCDFN 1.1mmX 0.7mm -6L	W	MSL1	ROHS+HF	3000 units/Tape & Reel

ABSOLUTE MAXIMUM RATINGS[1]

PARAMETERS	RANGE			
Supply voltage VCC	-0.3V to 3.6V			
EN pin voltage	-0.3V to 3.6V			
Supply maximum current ICC	30mA			
RF input power Pin	25dBm			
Maximum Junction temperature T _{JMAX}	150°C			
Storage temperature T _{STG}	-65°C to 150°C			
Operating free-air temperature range	-40°C to 85°C			
Lead temperature (Soldering 10 Seconds)	260℃			
ESD ^[2]				
HBM	±2kV			
CDM	±1kV			
Latch-up				
Standard: JEDEC STANDARD NO.78D NOVEMBER 2011	+IT: +200mA			
Statidard. JEDEC STANDARD NO.18D NOVEMBER 2011	-IT: -200mA			

^[1] Conditions out of those ranges listed in "absolute maximum ratings" may cause permanent damages to the device. In spite of the limits above, functional operation conditions of the device should within the ranges listed in "recommended operating conditions". Exposure to absolute-maximum-rated conditions for prolonged periods may affect device reliability.

^[2] The human body model is a 100pF capacitor discharged through a 1.5kΩ resistor into each pin. Test method: MIL-STD-883J Method 3015.9. The CDM test method: JEDEC EIA/JESD22-C101F.

ELECTRICAL CHARACTERISTICS

TA=+25°C , V_{CC}=2.8V, EN=1.8V/2.8V, frequency=2300MHz to 2690MHz. Input matched to 50Ω using a $3.3nH^{[3]}$ inductor in series. (unless otherwise noted).

Symbol	Parameter	Min	Тур	Max	Units		
DC Electi	rical Characteristic				•		
VCC	Supply Voltage		1.5	-	3.3	V	
	Digital Input-Logic High		0.8		3.3	V	
VEN	Digital Input-Logic Low				0.45	V	
Gain Mod	le						
ICC	Supply Current			9	12.5	mA	
		2300MHz-2400MHz	12	13.6	14.5		
		2400MHz-2496MHZ	12	13.2	14.5		
Gp	Power Gain	2496MHz-2690MHz	12	12.8	14.5	dB	
		f=2350MHz [4]	12	13.7	14.5		
		f=2655MHz [5]	12	13.0	14.5		
DLin	Input Deturn Less	f=2350MHz [4]	6	7		dD	
RLin Input Return Loss		f=2655MHz [5]	6	9		dB	
		f=2350MHz [4]	6	8		dB	
RLout	Output Return Loss	f=2655MHz [5]	6	7			
		f=2350MHz [4]	18	26			
ISL	Reverse Isolation	f=2655MHz [5]	18	26		dB	
		f=2350MHz [4][6]		1.0	1.4		
NF	Noise Figure	f=2655MHz [5][6]		1.3	1.4	dB	
	In-band input	f=2350MHz [4]	-6	-3			
IP1dB	1dB-compression point	f=2655MHz [5]	-6	-1		dBm	
UDO"	In-band input	f=2350MHz [4]	-0.5	5			
IIP3ib	3 rd -order intercept point	f=2655MHz [5]	-0.5	7.5		dBm	
ton	turn-on time	time from V _{EN} ON to 90% of the gain		2	4	μs	
toff	turn-off time	time from V _{EN} OFF to 10% of the gain		1	2	μs	
Bypass N	/lode						
ICC	Supply Current	VEN<0.45V			1	uA	
		2300MHz-2400MHz	-4.5	-3.8			
		2400MHz-2496MHz	-4.5	-3.5			
Gp	Power Gain	2496MHz-2690MHz	-4.5	-3.5		dB	
		f=2350MHz [4]	-4.5	-3.8			
		f=2655MHz [5]	-4.5	-3.5			
RLin	Input Return Loss	f=2350MHz [4]	6	9		dB	
INLIII	input Netuin Loss	f=2655MHz [5]	6	9		uБ	
RLout	Output Return Loss	f=2350MHz [4]	6	8.5		dB	



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Symbol	Parameter	Test Condition	Min	Тур	Max	Units
		f=2655MHz [5]	6	7.5		
	In-band input	f=2350MHz [4]	2 7		dBm	
IP1dB	1dB-compression point	f=2655MHz [5]	2	8		UDIII
	In-band input	f=2350MHz [4]	6	8		
IIP3ib	3 rd -order intercept point	f=2655MHz [5]	6	8		dBm

^[3] High quality-factor 3.3nH inductor.

TA=+25°C , V_{CC}=1.8V, EN=1.8V, frequency=2300MHz to 2690MHz. Input matched to 50Ω using a $3.3nH^{[3]}$ inductor in series. (unless otherwise noted).

Symbol	Parameter	Test Condition	Min	Тур	Max	Units	
DC Electi	rical Characteristic		•	•			
VCC	Supply Voltage		1.5	-	3.3	V	
	Digital Input-Logic High		0.8		3.3	V	
VEN	Digital Input-Logic Low				0.45	V	
Gain Mod	le						
ICC	Supply Current			8.0	10	mA	
		2300MHz-2400MHz	11.4	13.2	14		
		2400MHz-2496MHz	11.4	12.8	14		
Gp	Power Gain	2496MHz-2690MHz	11.4	12.5	14	dB	
-16	111(,)	f=2350MHz [4]	11.4	13.2	14		
		f=2655MHz [5]	11.4	12.5	14		
DLiv	Level Determine	f=2350MHz [4]	6	7		JD.	
RLin	Input Return Loss	f=2655MHz [5]	6	9		dB	
Dissi	0 + 10 + 1	f=2350MHz [4]	6	8			
RLout	Output Return Loss	f=2655MHz [5]	6	7		dB	
		f=2350MHz [4]	18	26	26		
ISL	Reverse Isolation	f=2655MHz [5]	18	26		dB	
		f=2350MHz [4][6]		1.0	1.4		
NF	Noise Figure	f=2655MHz [5][6]		1.3	1.4	dB	
	In-band input	f=2350MHz [4]	-6	-5.2			
IP1dB	1dB-compression point	f=2655MHz [5]	-6	-3.7		dBm	
	In-band input	f=2350MHz [4]	-0.5	3			
IIP3ib	3 rd -order intercept point	f=2655MHz [5]	-0.5	5		dBm	
ton	turn-on time	time from VEN ON to 90% of the gain		2	4	μs	
toff	turn-off time	time from V _{EN} OFF to 10% of the gain		1	2	μs	
Bypass N	/lode						
ICC	Supply Current	VEN<0.45V			1	uA	
Gp	Power Gain	2300MHz-2400MHz	-4.8	-4		dB	

^[4] E-UTRA operating band40(2300MHz to 2400MHz) , input power is-25dBm.

^[5] E-UTRA operating band 7(2620MHz to 2690MHz), input power is -25dBm.

^[6] PCB losses are subtracted.



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Symbol	Parameter	Test Condition	Min	Тур	Max	Units
		2400MHz-2496MHz	-4.8	-3.8		
		2496MHz-2690MHz	-4.8	-3.8		
		f=2350MHz [4]	-4.8	-4		
		f=2655MHz [5]	-4.8	-3.8		
	Input Potura Logo	f=2350MHz [4]	6	8.5		dB
RLin	Input Return Loss	f=2655MHz [5]	6	7.5		uБ
	Output Potura Logo	f=2350MHz [4]	6	8.5		dB
RLout	Output Return Loss	f=2655MHz [5]	6	7.5		uБ
	In-band input	f=2350MHz [4]	2	5		dBm
IP1dB	1dB-compression point	f=2655MHz [5]	2	5.5		UDIII
	In-band input	f=2350MHz [4]	5	7		
IIP3ib	3 rd -order intercept point	f=2655MHz [5]	5	7		dBm

^[3] High quality-factor 3.3nH inductor.

MEASUREMENT DIAGRAM

Test DC Characteristics(Current & Power Consumption)

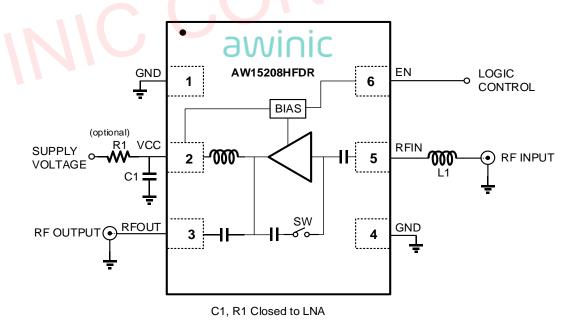


Figure 4 AW15208HFDR DC Test Diagram

^[4] E-UTRA operating band40(2300MHz to 2400MHz) , input power is -25dBm..

^[5] E-UTRA operating band 7(2620MHz to 2690MHz), input power is -25dBm.

^[6] PCB losses are subtracted.

Test S-Parameter

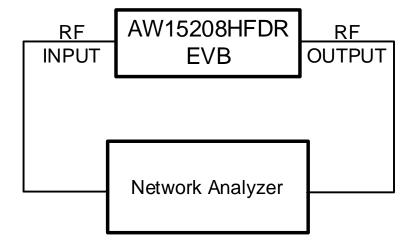


Figure 5 AW15208HFDR S-parameter Measurement Diagram

Test Noise Figure

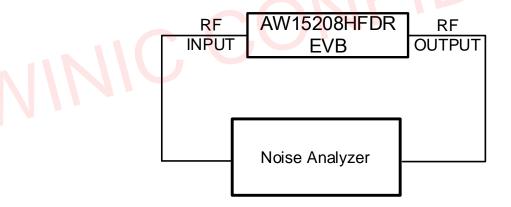


Figure 6 AW15208HFDR Noise Figure Measurement Diagram

Test IIP3

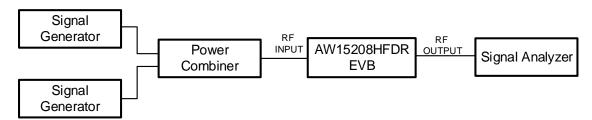


Figure 7 AW15208HFDR IIP3 Measurement Diagram



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APPLICATION INFORMATION

Choice of components

- The AW15208HFDR requires only one external inductor for input matching. If the device/phone manufacturers implement very good power supply filtering on their boards, the bypass capacitor mentioned in this application circuit may be optional. With the power supply decoupling capacitor, better performance would be received, like a little higher gain, etc. The value is optimized for the key performance, such as higher power gain, lower noise figure, and better return loss. Typical value of inductor is 3.3nH with high quality factor, and capacitor is 1nF. The typical application circuit can refer to Figure 1.
- The output of AW15208HFDR is internally matched to 50 ohm and a DC blocking capacitor is integrated on-chip, thus no external component is required at the output.
- The AW15208HFDR should be placed close to the diversity antenna with the inputmatching inductor. Use 50 ohm micro-strip lines to connect RF INPUT and RF OUTPUT. Bypass capacitor need be located close to the device. For long Vcc lines, it may be necessary to add more decoupling capacitors. Proper grounding of the GND pins is very important.

Following tables show recommended inductor and capacitor values.

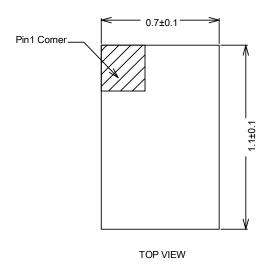
Inductor Selection Table

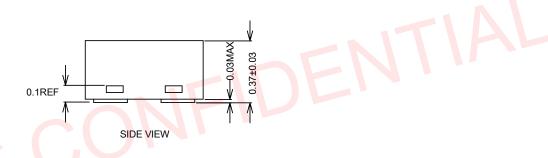
Component	Part	Typical(nH)	Q(min)	Frequency(MHz)	MFR	Size
L1	LQW15A	3.3	25	250	Murata	0402

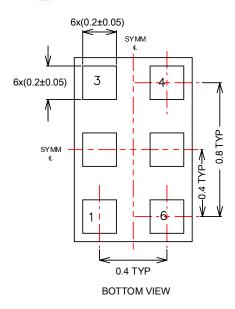
Capacitor Selection Table

Component	Part	Typical(pF)	Voltage(V)	MFR	Size
C1	GRM155	1000	50	Murata	0402

PACKAGE DESCRIPTION



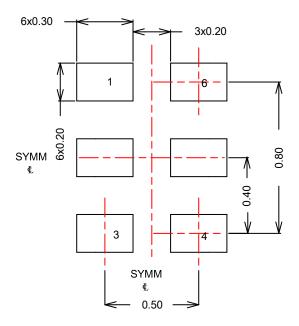


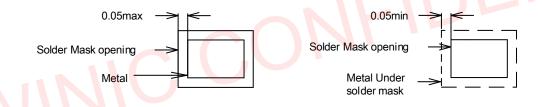


Unit: mm

Figure 8 Package Outline

LAND PATTERN





Non-solder Mask Defined

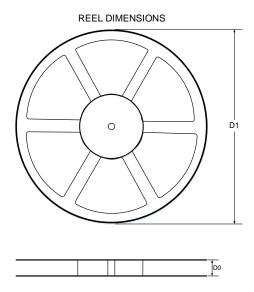
Solder Mask Defined

Unit: mm

Figure 9 Land Pattern



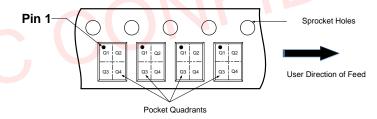
TAPE & REEL DESCRIPTION



TAPE DIMENSIONS

- A0: Dimension designed to accommodate the component width
- B0: Dimension designed to accommodate the component length
- K0: Dimension designed to accommodate the component thickness
- W: Overall width of the carrier tape
- P0: Pitch between successive cavity centers and sprocket hole
- P1: Pitch between successive cavity centers
- P2: Pitch between sprocket hole
- D1: Reel Diameter
- D0: Reel Width

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



DIMENSIONS AND PIN1 ORIENTATION

D1	D0	A0	B0	K0	P0	P1	P2	W	Pin1 Quadrant	
(mm)	Pili i Quadrant									
178	8.4	0.8	1.2	0.55	2	2	4	8	Q1	

All dimensions are nominal

Figure 10 **Tape & Reel Description**



REVISION HISTORY

Version	Date	Change Record
V1.0	Mar.2019	Officially Released
V1.1	Oct.2019	Update electrical characteristics
V1.2	Oct.2019	Update electrical characteristics
V1.3	Nov.2019	Update electrical characteristics





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